

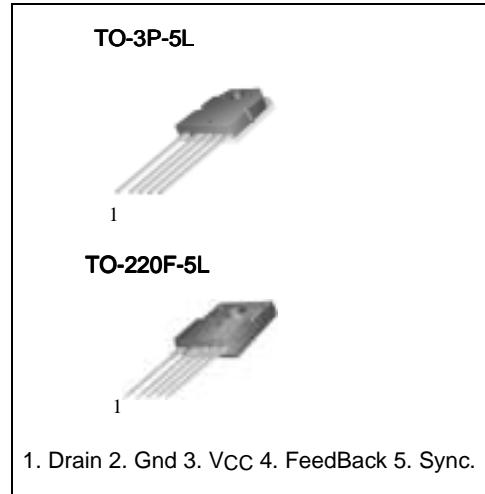
# FS6S-SERIES

## FS6S0965R/FS6S0965RT/FS6S1265RB

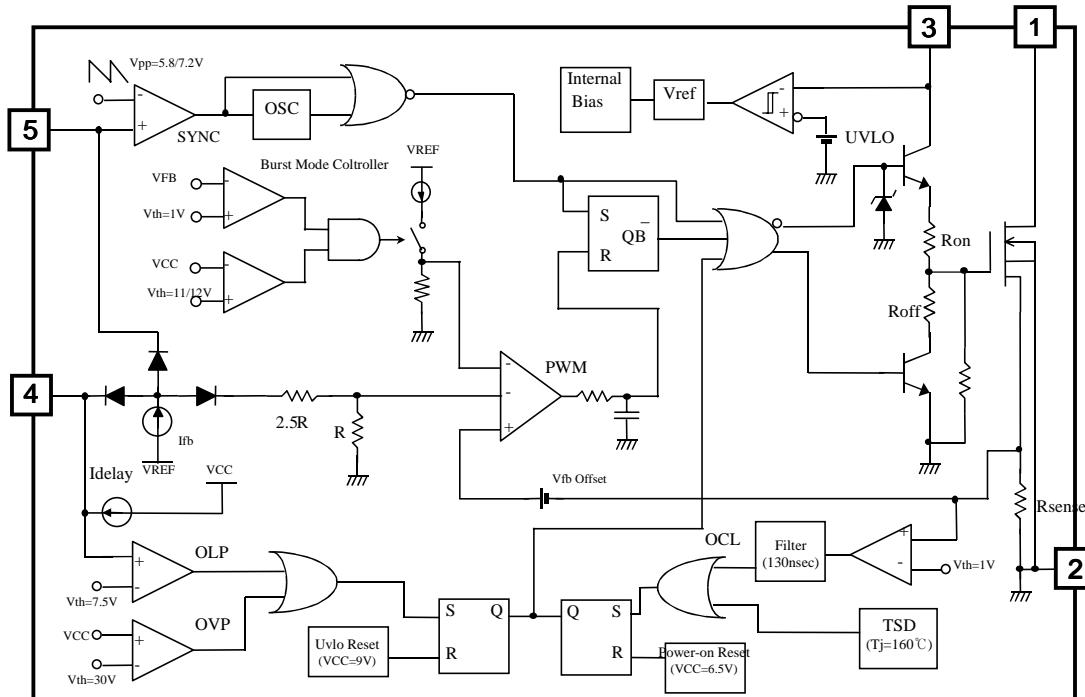
### Fairchild Power Switch(FPS)

#### Features

- Wide Operating Frequency Range Up to 150Khz
- Lowest Cost SMPS Solution
- Lowest External Components
- Low Start up Current (max:170uA)
- Low Operating Current (max:15mA)
- Internal High Voltage SenseFET
- Built-in Auto Restart Circuit
- Over Voltage Protection (Auto Restart Mode)
- Over Load Protection (Auto Restart Mode)
- Over Current Protection With Latch Mode
- Internal Thermal Protection With Latch Mode
- Pulse By Pulse Over Current Limiting
- Internal Burst Mode Controller for Stand-by Mode
- Under Voltage Lockout With Hysteresis
- External Sync. Terminal



#### Internal Block Diagram



**Absolute Maximum Ratings**

(Ta=25°C, unless otherwise specified)

Characteristic	Symbol	Value	Unit
<b>FS6S0965RT/FS6S0965R</b>			
Drain to PKG Breakdown Voltage	BVPKG	FS6S0965RT	3500
Maximum Drain Voltage	V <sub>D,MAX</sub>	650	V
Drain-Gate Voltage(RGS=1MΩ)	V <sub>DGR</sub>	650	V
Gate-Source(GND) Voltage	V <sub>GS</sub>	±30	V
Drain Current Pulsed <sup>(1)</sup>	I <sub>DM</sub>	36	ADC
Continuous Drain Current (Tc = 25°C)	I <sub>D</sub>	9	ADC
Continuous Drain Current (Tc = 100°C)	I <sub>D</sub>	7.2	ADC
Single Pulsed Avalanche Current(Energy <sup>(2)</sup> )	I <sub>AS(EAS)</sub>	25(950)	A(mJ)
Maximum Supply Voltage	V <sub>CC,MAX</sub>	35	V
Input Voltage Range	V <sub>FB</sub>	-0.3 to V <sub>CC</sub>	V
	V <sub>SS</sub>	-0.3 to 10	V
Total Power Dissipation	PD (Watt H/S)	FS6S0965RT	48
		FS6S0965R	170
	Derating	FS6S0965RT	0.385
		FS6S0965R	1.33
Operating Junction Temperature.	T <sub>J</sub>	+160	°C
Operating Ambient Temperature.	T <sub>A</sub>	-25 to +85	°C
Storage Temperature Range.	T <sub>TSG</sub>	-55 to +150	°C

<b>FS6S1265RB</b>			
Characteristic	Symbol	Value	Unit
Maximum Drain Voltage	V <sub>D,MAX</sub>	650	V
Drain-Gate Voltage(RGS=1MΩ)	V <sub>DGR</sub>	650	V
Gate-Source(GND) Voltage	V <sub>GS</sub>	±30	V
Drain Current Pulsed <sup>(1)</sup>	I <sub>DM</sub>	48	ADC
Continuous Drain Current (Tc = 25°C)	I <sub>D</sub>	12	ADC
Continuous Drain Current (Tc = 100°C)	I <sub>D</sub>	8.4	ADC
Single Pulsed Avalanche Current(Energy <sup>(2)</sup> )	I <sub>AS(EAS)</sub>	30(950)	A(mJ)
Maximum Supply Voltage	V <sub>CC,MAX</sub>	35	V
Input Voltage Range	V <sub>FB</sub>	-0.3 to V <sub>CC</sub>	V
	V <sub>SS</sub>	-0.3 to 10	V
Total Power Dissipation	PD (Watt H/S)	240	W
		Derating	1.92
Operating Junction Temperature.	T <sub>J</sub>	+160	°C
Operating Ambient Temperature.	T <sub>A</sub>	-25 to +85	°C
Storage Temperature Range.	T <sub>TSG</sub>	-55 to +150	°C

## Electrical Characteristics (SFET Part)

(Ta = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>FS6S0965RT/FS6S0965R</b>						
Drain Source Breakdown Voltage	BVDSS	VGS = 0V, ID = 50µA	650	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS=Max., Rating, VGS=0V	-	-	200	µA
		VDS= 0.8Max., Rating, VGS = 0V, TC = 125°C	-	-	300	µA
Static Drain-Source On Resistance <sup>(1)</sup>	RDS(on)	VGS = 10V, ID = 4.5A	-	1.1	1.2	Ω
Forward transconductance <sup>(1)</sup>	gfs	VDS = 50V, ID = 4.5A	-	-	-	S
Input capacitance	Ciss	VGS = 0V, VDS = 25V, f = 1MHz	-	1300	-	pF
Output capacitance	Coss		-	135	-	
Reverse transfer capacitance	Crss		-	25	-	
Turn on delay time	td(on)	VDD = 0.5BVDSS, ID = 9.0A (MOSFET switching time are essentially independent of operating temperature)	-	25	-	nS
Rise time	tr		-	75	-	
Turn off delay time	td(off)		-	130	-	
Fall time	tf		-	70	-	
Total gate charge (gate-source+gate-drain)	Qg	VGS = 10V, ID = 9.0A, VDS = 0.5BVDSS(MOSFET Switching time are Essentially independent of Operating temperature)	-	45	-	nC
Gate-source charge	Qgs		-	8	-	
Gate-drain (Miller) charge	Qgd		-	22	-	
<b>FS6S1265RB</b>						
Drain-Source Breakdown Voltage	BVDSS	VGS = 0V, ID = 50µA	650	-	-	V
Zero Gate Voltage Drain Current	IDSS	VDS=Max, Rating, VGS = 0V	-	-	200	µA
		VDS= 0.8Max, Rating, VGS = 0V, TC = 125°C	-	-	300	µA
Static Drain-Source On Resistance <sup>(1)</sup>	RDS(on)	VGS = 10V, ID = 4.5A	-	0.7	0.9	Ω
Forward transconductance <sup>(1)</sup>	gfs	VDS = 50V, ID = 4.5A	-	-	-	S
Input capacitance	Ciss	VGS = 0V, VDS = 25V, f = 1MHz	-	1820	-	pF
Output capacitance	Coss		-	185	-	
Reverse transfer capacitance	Crss		-	32	-	
Turn on delay time	td(on)	VDD = 0.5BVDSS, ID = 12.0A (MOSFET switching time are essentially independent of operating temperature)	-	38	-	nS
Rise time	tr		-	120	-	
Turn off delay time	td(off)		-	200	-	
Fall time	tf		-	100	-	
Total gate charge (gate-source+gate-drain)	Qg	VGS = 10V, ID = 12.0A, VDS = 0.5BVDSS(MOSFET Switching time are Essentially independent of Operating temperature)	-	60	-	nC
Gate-source charge	Qgs		-	10	-	
Gate-drain (Miller) charge	Qgd		-	30	-	

**Electrical Characteristics (CONTROL Part)**

(VCC=16V, Tamb = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>UVLO SECTION</b>						
Start Threshold Voltage	VSTART	VFB=GND	14	15	16	V
Stop Threshold Voltage	VSTOP	VFB=GND	8	9	10	V
<b>OSCILLATOR SECTION</b>						
Initial Frequency	FOSC	-	22	25	28	kHz
Voltage Stability	FSTABLE	12V ≤ VCC ≤ 23V	0	1	3	%
Temperature Stability (Note2)	ΔFOSC	-25°C ≤ Ta ≤ 85°C	0	±5	±10	%
Maximum Duty Cycle	D <sub>MAX</sub>	-	92	95	98	%
Minimum Duty Cycle	D <sub>MIN</sub>	-	-	-	0	%
<b>FEEDBACK SECTION</b>						
Feedback Source Current	I <sub>FB</sub>	VFB=GND	0.7	0.9	1.1	mA
Shutdown Feedback Voltage	V <sub>SD</sub>	VFB ≥ 6.9V	6.9	7.5	8.1	V
Shutdown Delay Current	I <sub>DELAY</sub>	VFB=5V	1.6	2.0	2.4	μA
<b>SYNC. &amp; SOFTSTART SECTION</b>						
Softstart Voltage	V <sub>SS</sub>	VFB=2V	4.7	5.0	5.3	V
Softstart Current	I <sub>SS</sub>	V <sub>SS</sub> =0V	0.8	1.0	1.2	mA
Sync High Threshold Voltage(Note3)	V <sub>SYNCH</sub>	VCC=16V , VFB=5V	-	7.2	-	V
Sync Low Threshold Voltage(Note3)	V <sub>SYNCL</sub>	VCC=16V , VFB=5V	-	5.8	-	V
<b>BURST MODE SECTION</b>						
Burst Mode Low Threshold Voltage	V <sub>BURL</sub>	VFB=0V	10.4	11.0	11.6	V
Burst Mode High Threshold Voltage	V <sub>BURH</sub>	VFB=0V	11.4	12.0	12.6	V
Burst Mode Enable Feedback Voltage	V <sub>BEN</sub>	VCC=10.5V	0.7	1.0	1.3	V
Burst Mode Peak Current Limit(Note4)	I <sub>BURPK</sub>	VCC=10.5V , VFB=0V	0.6	0.85	1.1	A
Burst Mode Frequency	F <sub>BUR</sub>	VCC=10.5V , VFB=0V	40	50	60	kHz
<b>CURRENT LIMIT(SELF-PROTECTION)SECTION</b>						
Peak Current Limit (Note4)	I <sub>OVER</sub>	FS6S0965R	5.28	6.0	6.72	A
		FS6S1265RB	7.04	8.0	8.96	
<b>PROTECTION SECTION</b>						
Over Voltage Protection	V <sub>OVP</sub>	V <sub>CC</sub> ≥ 27V	27	30	33	V
Over Current Latch voltage(Note3)	V <sub>OCL</sub>	-	0.9	1.0	1.1	V
Thermal Shutdown Temperature(Note2)	T <sub>SD</sub>	-	140	160	-	°C
<b>TOTAL DEVICE SECTION</b>						
Start Up Current	I <sub>START</sub>	V <sub>FB</sub> = GND, V <sub>CC</sub> = 14V	-	0.1	0.17	mA
Operating Supply Current(Note1)	I <sub>OP</sub>	V <sub>FB</sub> = GND, V <sub>CC</sub> = 16V	-	10	15	mA
	I <sub>OP(MIN)</sub>	V <sub>FB</sub> = GND, V <sub>CC</sub> = 12V				
	I <sub>OP(MAX)</sub>	V <sub>FB</sub> = GND, V <sub>CC</sub> = 30V				

**Notes:**

- These parameters are the Current Flowing in the Control IC.
- These parameters, although guaranteed, are not 100% tested in production
- These parameters, although guaranteed, are tested in EDS(wafer test) process
- These parameters are indicated Inductor Current.

## Typical Performance Characteristics

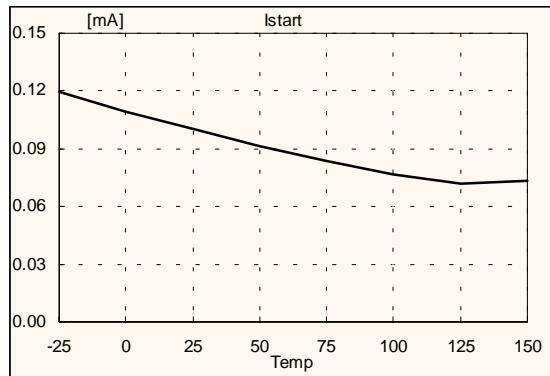


Figure 1. Start Up Current vs. Temp.

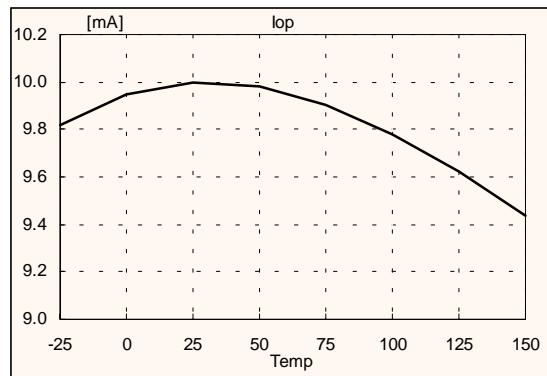


Figure 2. Operating Supply Current vs. Temp.

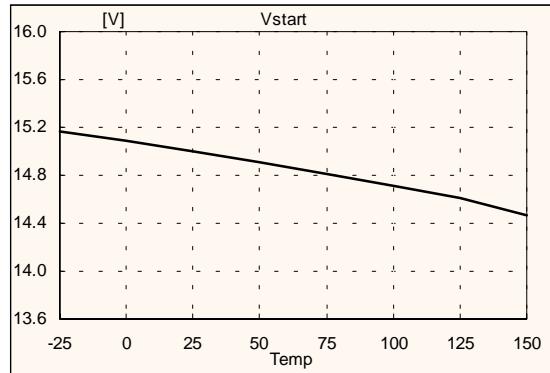


Figure 3. Start Threshold Voltage vs. Temp.

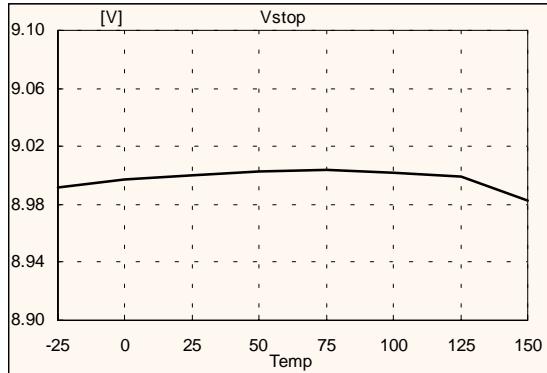


Figure 4. Stop Threshold Voltage vs. Temp.

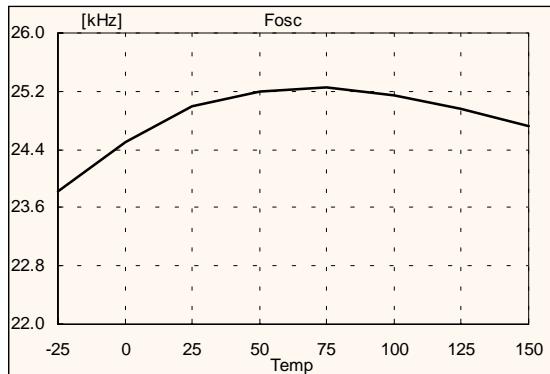


Figure 5. Initial Frequency vs. Temp.

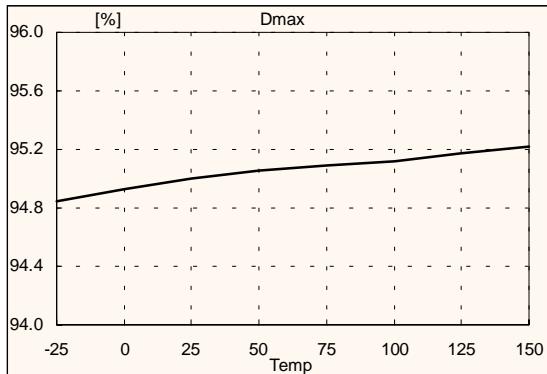


Figure 6. Maximum Duty vs. Temp.

## Typical Performance Characteristics (Continued)

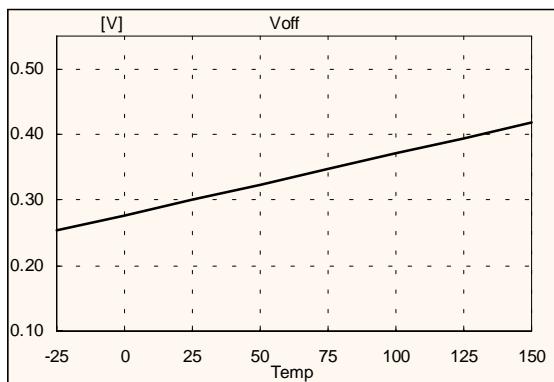


Figure 7. Feedback Offset Voltage vs. Temp.

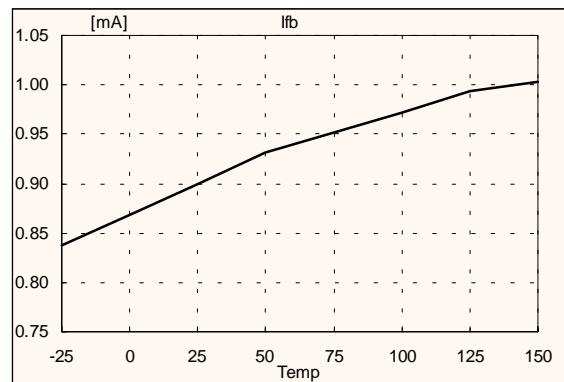


Figure 8. Feedback Source Current vs. Temp.

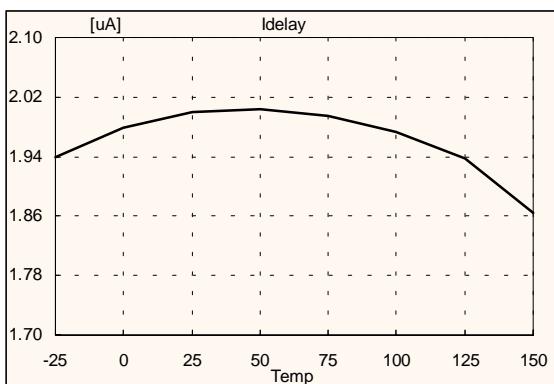


Figure 9. Shutdown Delay Current vs. Temp.

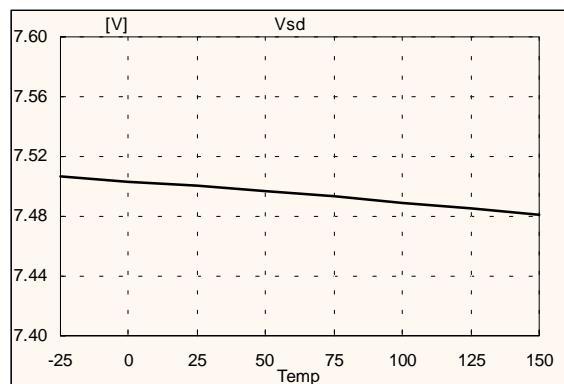


Figure 10. Shutdown Feedback Voltage vs. Temp.

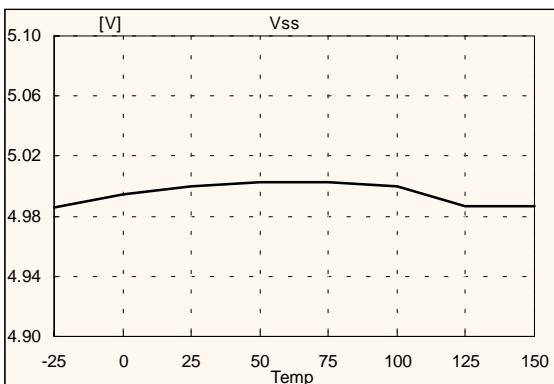


Figure 11. Softstart Voltage vs. Temp.

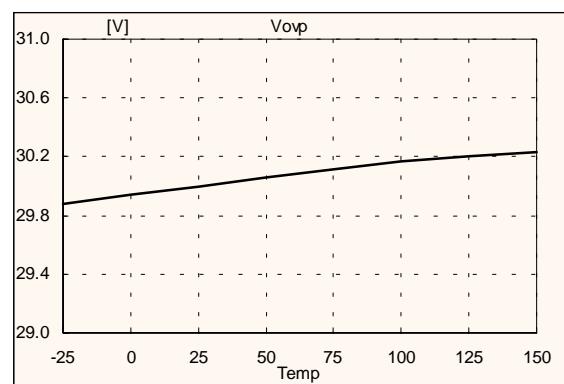


Figure 12. Over Voltage Protection vs. Temp.

## Typical Performance Characteristics (Continued)

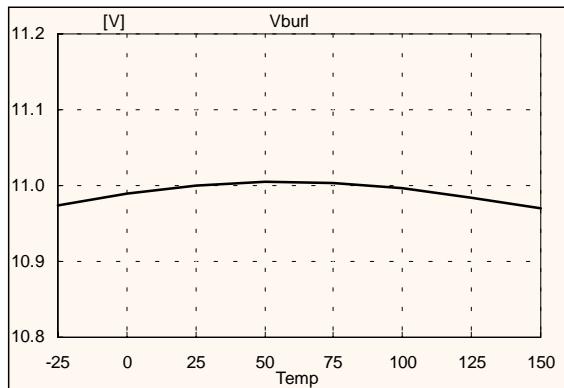


Figure 13. Burst Mode Low Voltage vs. Temp.

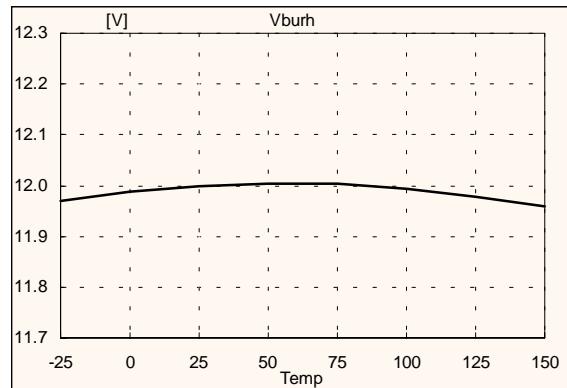


Figure 14. Burst Mode High Voltage vs. Temp.

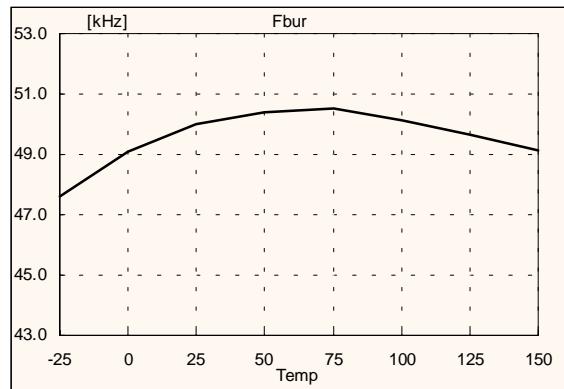


Figure 15. Burst Mode Frequency vs. Temp.

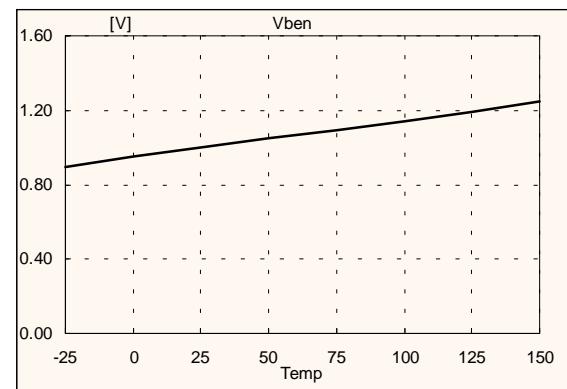


Figure 16. Burst Mode Enable Voltage vs. Temp.

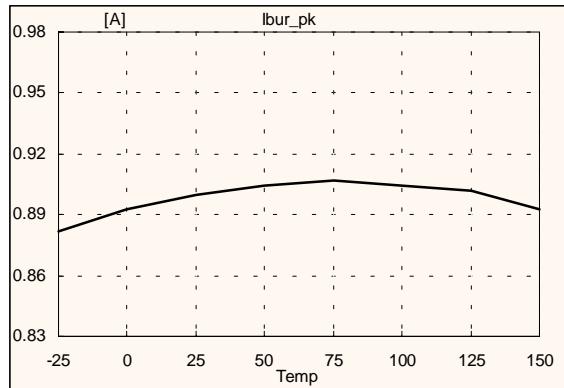


Figure 17. Burst Mode Peak Current vs. Temp.

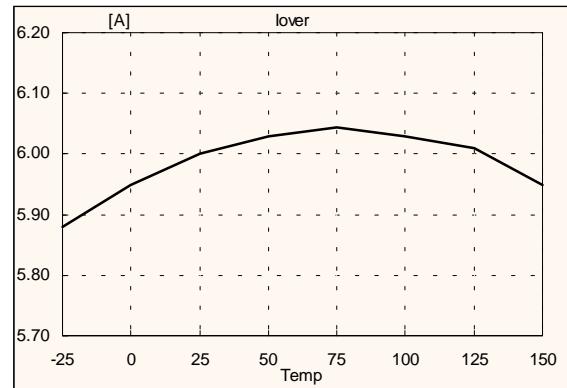
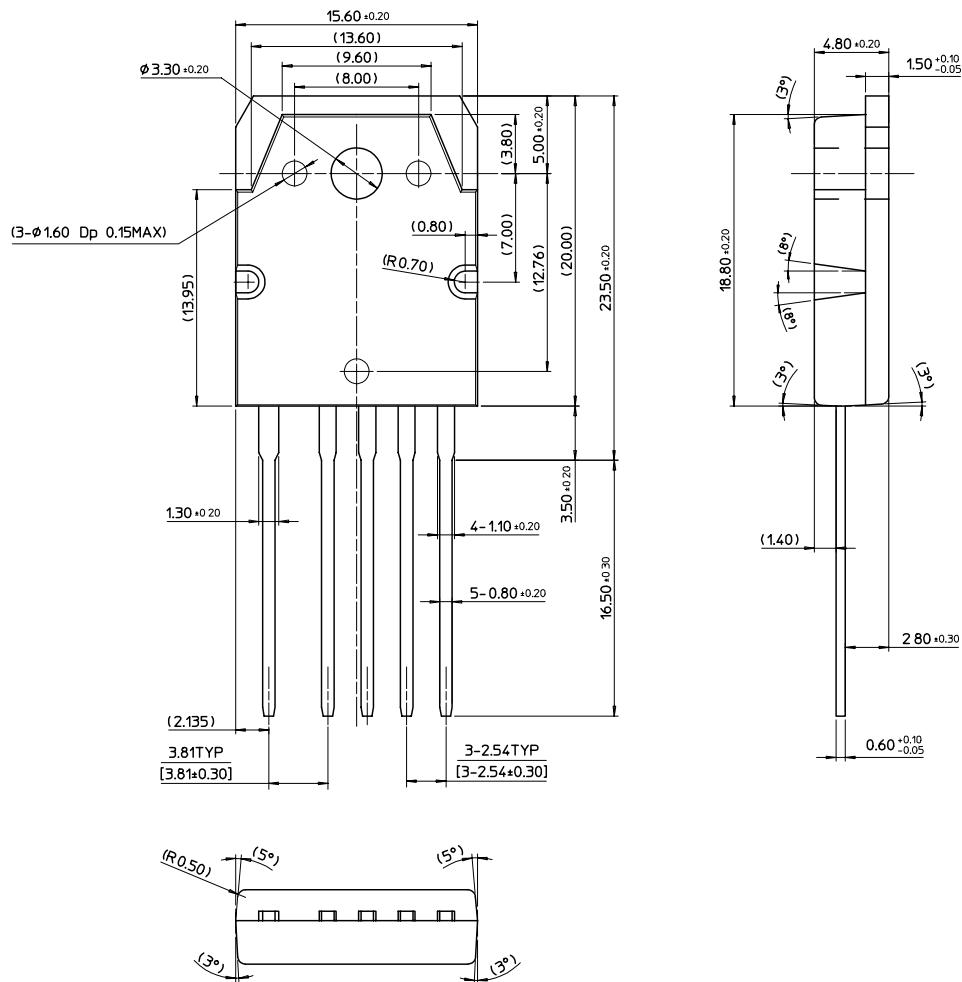


Figure 18. Peak Current Limit vs. Temp.

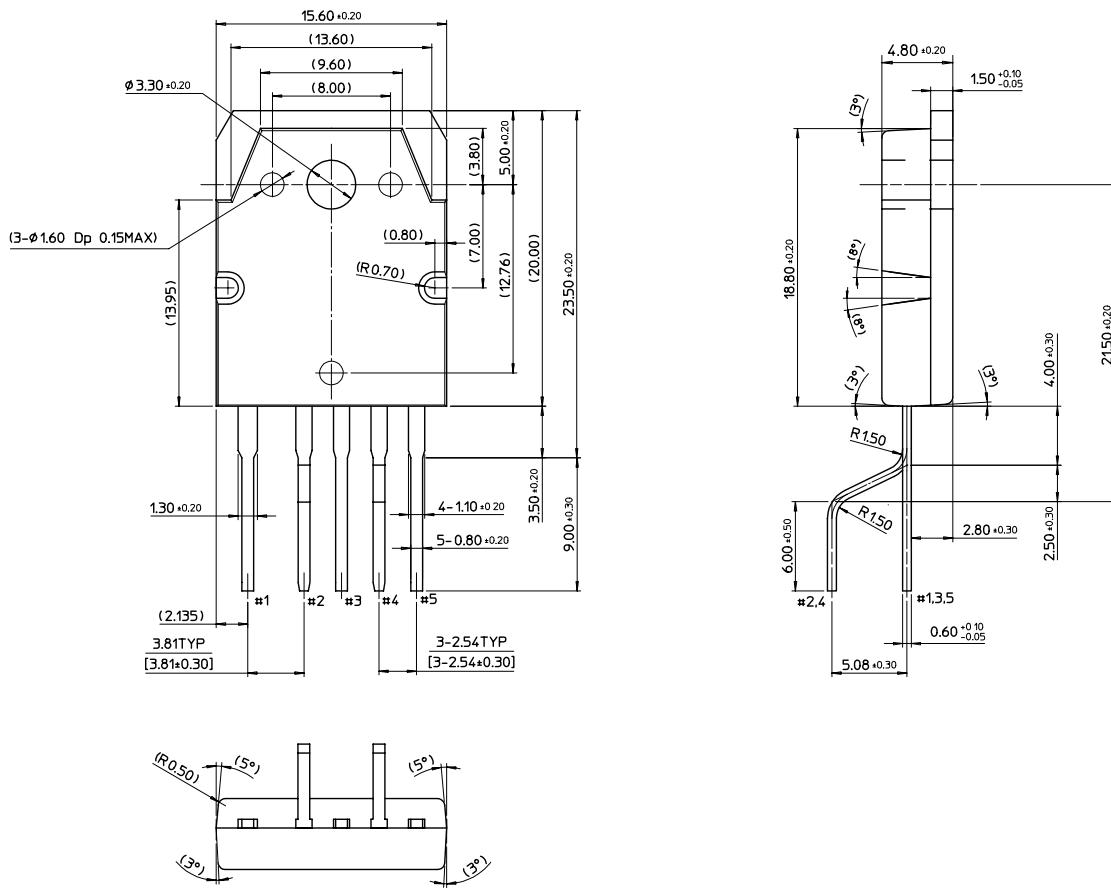
## Package Dimensions

**TO-3P-5L**



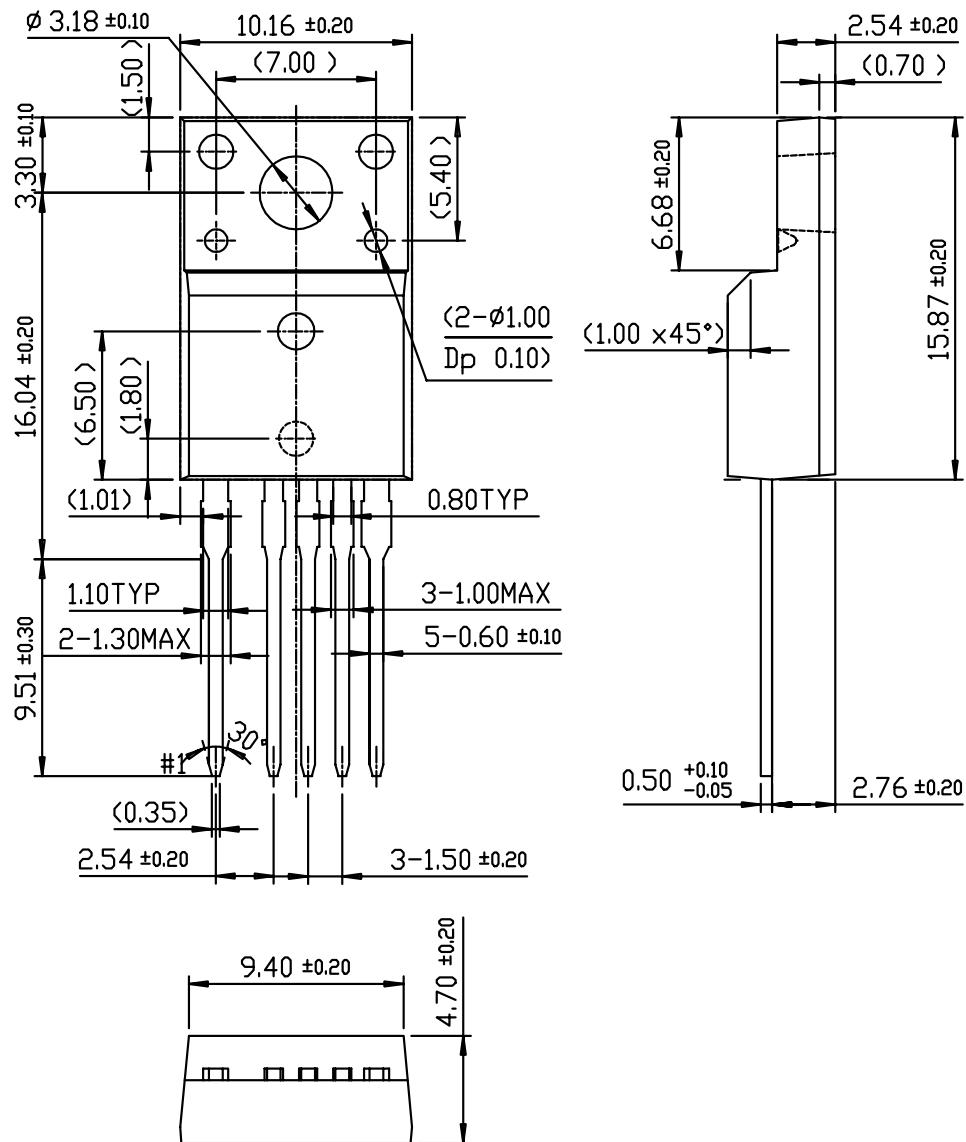
## Package Dimensions (Continued)

### TO-3P-5L (Forming)



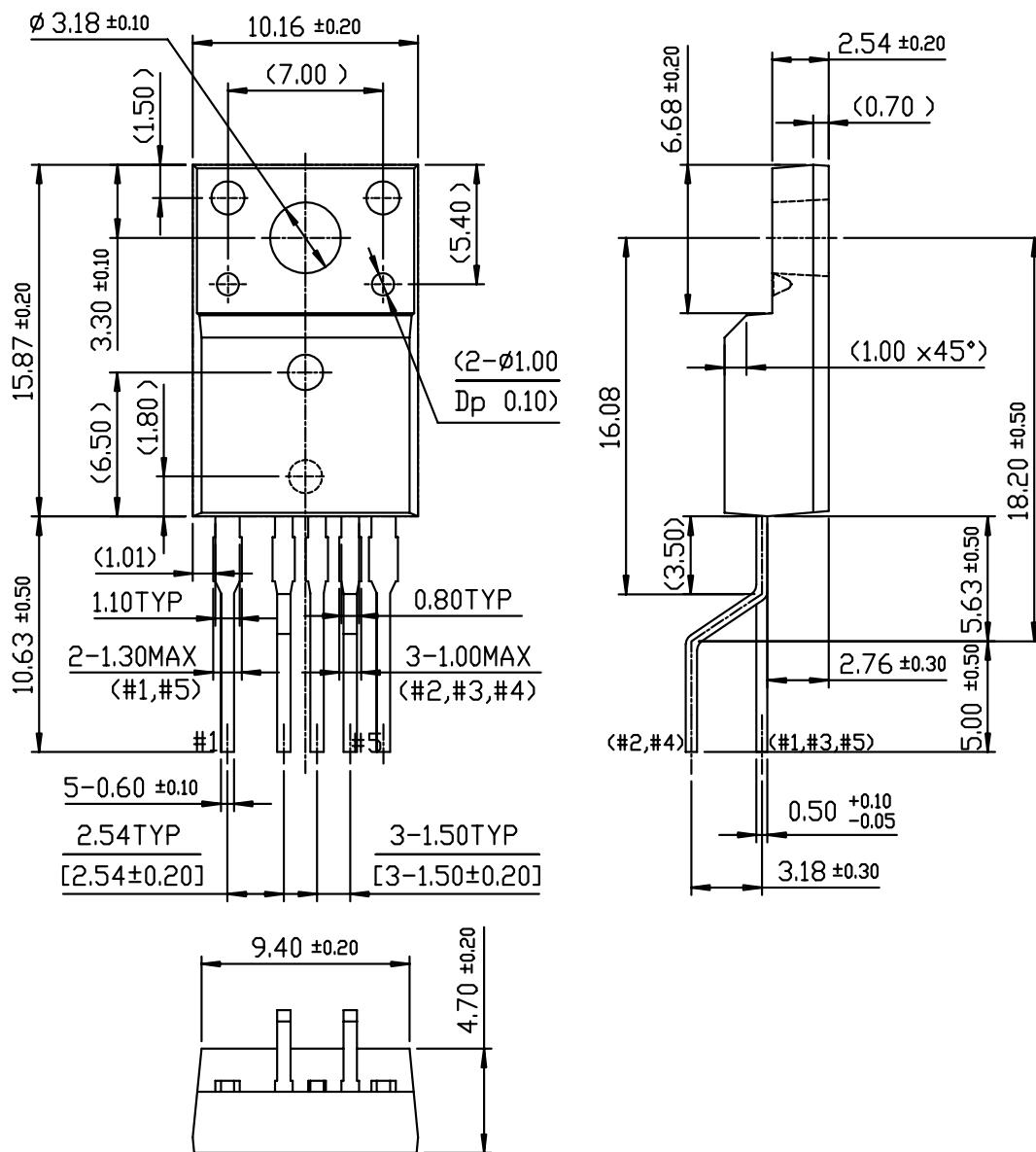
## Package Dimensions (Continued)

**TO-220F-5L**

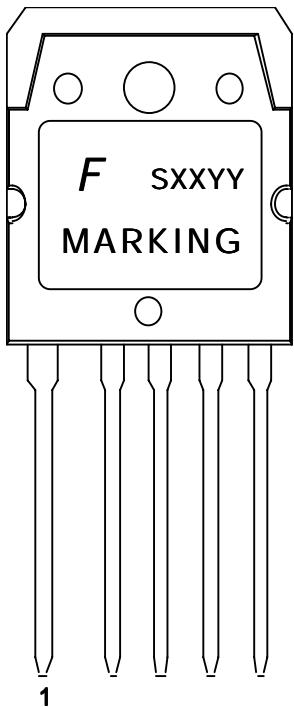


## Package Dimensions (Continued)

### TO-220F-5L(Forming)



## TOP Mark and Pinout Information



Pin No.	Symbol	Description
1	Drain	SenseFET Drain
2	GND	Ground (Source)
3	VCC	Control Part Supply Input
4	F/B	PWM Non Inverting Input
5	S/S	Soft start & External Sync.

Device	Marking
FS6S0965R	6S0965R
FS6S0965RT	
FS6S1265R	6S1265RB

### Notes:

- (1) F : Fairchild Semiconductor
- (2) 6S0965R, 6S1265RB : Device Marking Name
- (3) S : Plant Code (FPS: S)
- (4) XX : Patweek Based on Fairchild Semiconductor Work Month Calendar
- (5) YY : Last Two Digit of Calender Year

## Ordering Information

Product Number	Package	Marking Code	BVdss	Rds(on)
FS6S0965R-TU	TO-3P-5L	6S0965R	650V	1.1Ω
FS6S0965R-YDTU	TO-3P-5L(Forming)			
FS6S0965RT-TU	TO-220F-5L	6S0965R	650V	1.1Ω
FS6S0965RT-YDTU	TO-220F-5L(Forming)			
FS6S1265RB-TU	TO-3P-5L	6S1265RB	650V	0.7Ω
FS6S1265RB-YDTU	TO-3P-5L(Forming)			

TU : Non Forming Type

YDTU : Forming Type

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2. A critical component in any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.